MOSFETs Silicon N-Channel MOS (U-MOSVII-H)

# **TPCC8067-H**

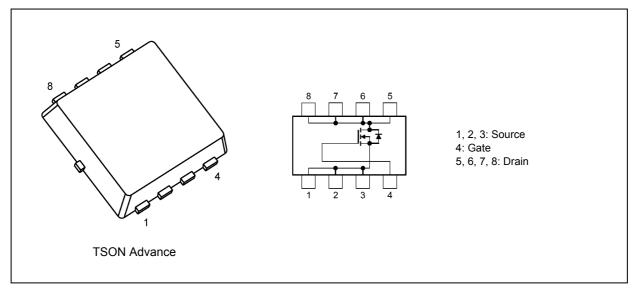
#### 1. Applications

- High-Efficiency DC-DC Converters
- Notebook PCs
- Mobile Handsets

#### 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 1.9 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 26 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 4.5 \text{ V})$
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteri                    | Symbol                  | Rating   | Unit             |            |    |
|-------------------------------|-------------------------|----------|------------------|------------|----|
| Drain-source voltage          |                         |          | V <sub>DSS</sub> | 30         | V  |
| Gate-source voltage           |                         |          | V <sub>GSS</sub> | ±20        |    |
| Drain current (DC)            |                         | (Note 1) | Ι <sub>D</sub>   | 9          | Α  |
| Drain current (pulsed)        |                         | (Note 1) | I <sub>DP</sub>  | 27         |    |
| Power dissipation             | (T <sub>c</sub> = 25°C) |          | PD               | 15         | W  |
| Power dissipation             | (t = 10 s)              | (Note 2) | PD               | 1.9        | W  |
| Power dissipation             | (t = 10 s)              | (Note 3) | PD               | 0.7        | W  |
| Single-pulse avalanche energy |                         | (Note 4) | E <sub>AS</sub>  | 21         | mJ |
| Avalanche current             |                         |          | I <sub>AR</sub>  | 9          | Α  |
| Channel temperature           |                         |          | T <sub>ch</sub>  | 150        | °C |
| Storage temperature           |                         |          | T <sub>stg</sub> | -55 to 150 |    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       |                         |          | Symbol                | Max  | Unit |
|---------------------------------------|-------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | (T <sub>c</sub> = 25°C) |          | R <sub>th(ch-c)</sub> | 8.33 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)              | (Note 2) | R <sub>th(ch-a)</sub> | 65.7 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)              | (Note 3) | R <sub>th(ch-a)</sub> | 178  | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V<sub>DD</sub> = 24 V, T<sub>ch</sub> = 25°C (initial), L = 0.2 mH, R<sub>G</sub> = 1.2  $\Omega$ , I<sub>AR</sub> = 9 A

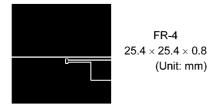


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

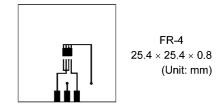


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

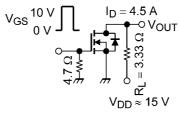
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                  | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V                |     |      | ±0.1 | μA   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V   |     |      | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 30  | _    | —    | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V | 15  | _    | _    |      |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA | 1.3 | _    | 2.3  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 4.5 A |     | 26   | 33   | mΩ   |
|                                |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A  |     | 20   | 25   |      |

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 690  | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | ]  |     | 28   | _   |      |
| Output capacitance             | C <sub>oss</sub> | ]  | _   | 120  | _   |      |
| Gate resistance                | r <sub>g</sub>   | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 5 MHz               | _   | 3.4  | 5.1 | Ω    |
| Switching time (rise time)     | tr               | See Figure 6.2.1.  | _   | 2.1  | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  | ]  | _   | 6.5  | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   | ]  |     | 2.0  |     |      |
| Switching time (turn-off time) | t <sub>off</sub> | ]  |     | 14   | _   |      |



Duty  $\leq$  1%,  $t_W$  = 10  $\mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                     | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | Qg               | $V_{DD} \approx 24$ V, $V_{GS}$ = 10 V, $I_D$ = 9 A                                       | _   | 9.5  | _   | nC   |
| gate-drain)                         |                  | $V_{DD} \approx 24$ V, $V_{GS}$ = 5 V, $I_D$ = 9 A  | _   | 4.7  | _   |      |
| Gate-source charge 1                | Q <sub>gs1</sub> | $V_{DD} \approx 24 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 9 \text{ A}$ | _   | 2.2  | _   |      |
| Gate-drain charge                   | Q <sub>gd</sub>  |   | _   | 0.9  | —   |      |
| Gate switch charge                  | Q <sub>SW</sub>  |   | _   | 1.9  | _   |      |

### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                         | Symbol           | Test Condition                               | Min | Тур. | Max  | Unit |
|---|------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 5) | I <sub>DRP</sub> | —  | _   | —    | 27   | А    |
| Diode forward voltage                   | V <sub>DSF</sub> | I <sub>DR</sub> = 9 A, V <sub>GS</sub> = 0 V |     | _    | -1.2 | V    |

Note 5: Ensure that the channel temperature does not exceed 150°C.

7. Marking

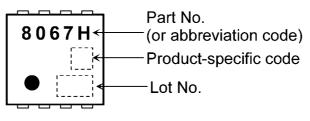
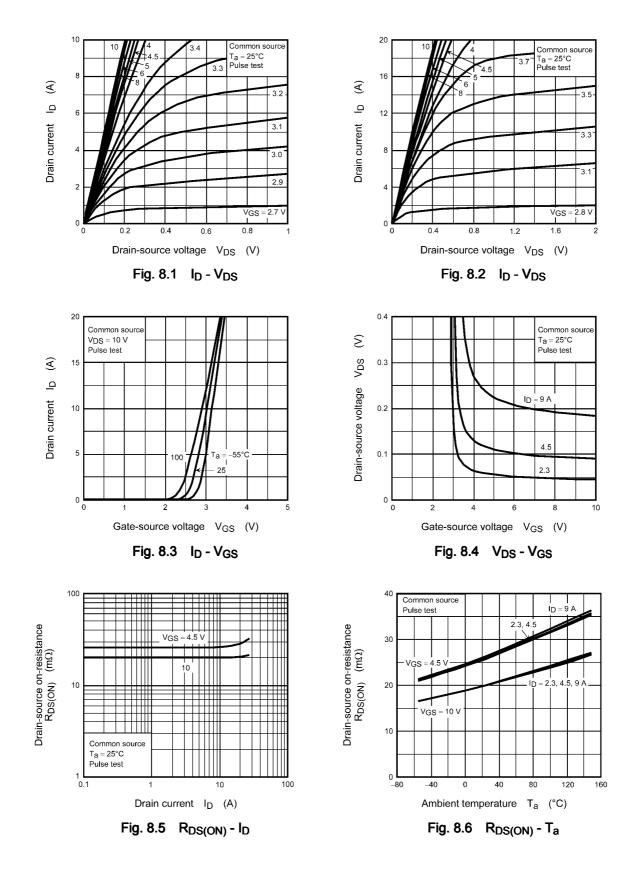


Fig. 7.1 Marking

### 8. Characteristics Curves (Note)

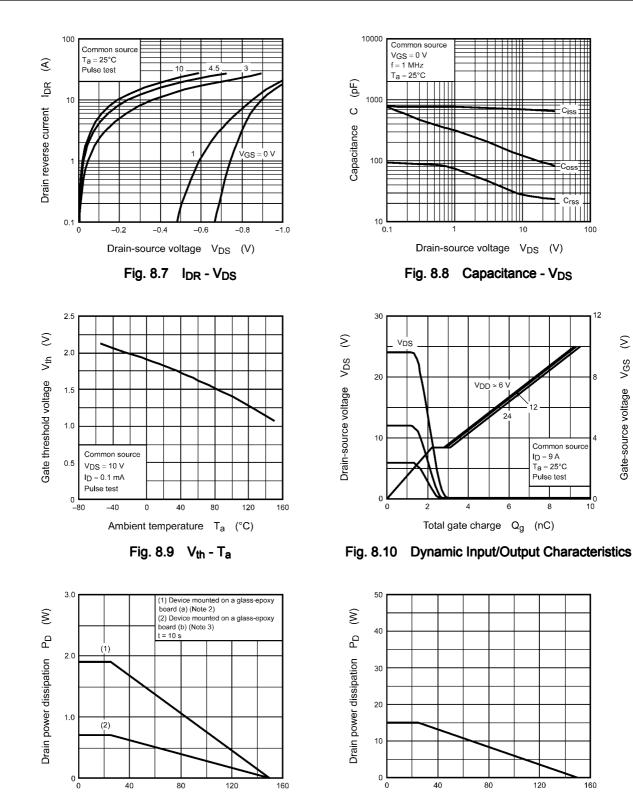


12

**0** 10

S

Gate-source voltage V<sub>GS</sub>



Ambient temperature Ta (°C) Fig. 8.11 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

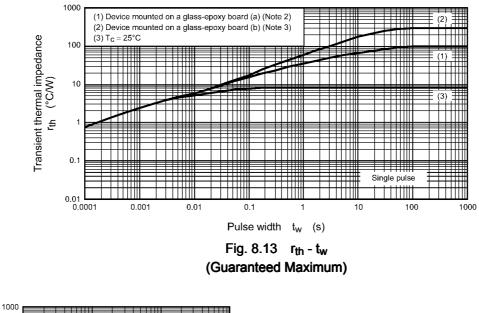
> 2011-06-02 Rev.2.0

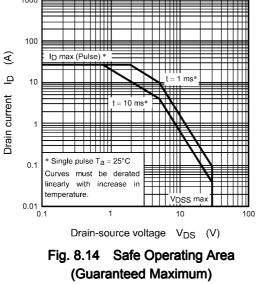
Case temperature  $T_c$  (°C)

Fig. 8.12 P<sub>D</sub> - T<sub>c</sub>

(Guaranteed Maximum)





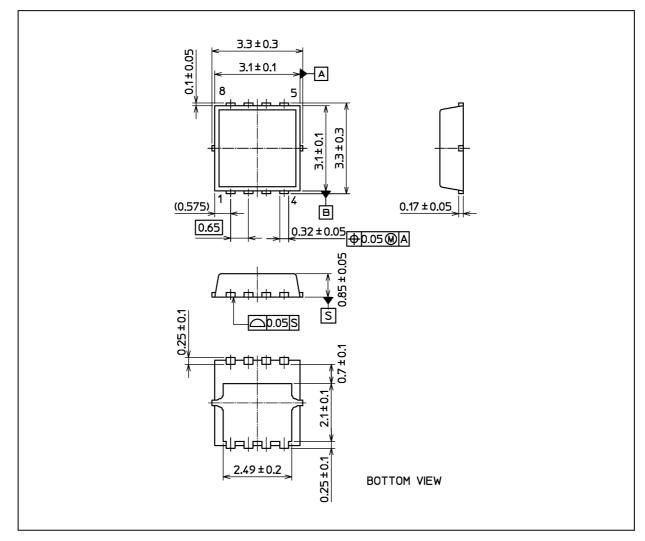


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPCC8067-H

#### Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

| Package Name(s)        |
|------------------------|
| TOSHIBA: 2-3X1S        |
| Nickname: TSON Advance |

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